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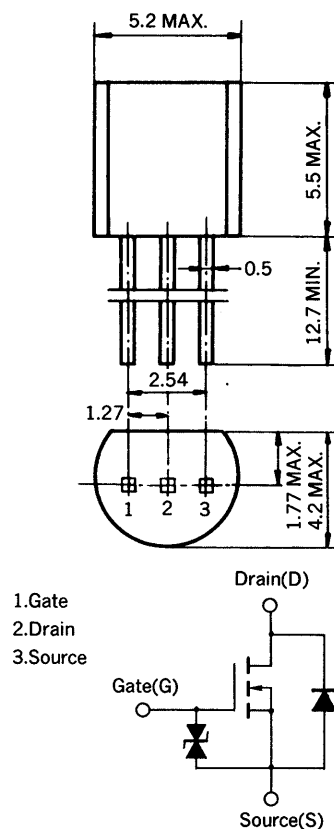
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MOS FIELD EFFECT TRANSISTOR

2SK1272

N-CHANNEL MOS FET FOR HIGH SPEED SWITCHING

PACKAGE DIMENSIONS (Unit : mm)



(Diode in the figure is the parasitic diode.)

The 2SK1272, N-channel vertical type MOS FET, is a switching device which can be driven directly by the output of ICs having a 5 V power source.

The MOS FET has excellent switching characteristics and is suitable for use as a high-speed switching device in digital circuits.

FEATURES

- Directly driven by ICs having a 5 V power source.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Low ON-state resistance

$$R_{DS(on)} = 1.00 \, \Omega \text{ TYP. at } V_{GS} = 4 \text{ V, } I_D = 0.5 \text{ A}$$

$$R_{DS(on)} = 0.65 \, \Omega \text{ TYP. at } V_{GS} = 10 \text{ V, } I_D = 0.5 \text{ A}$$

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

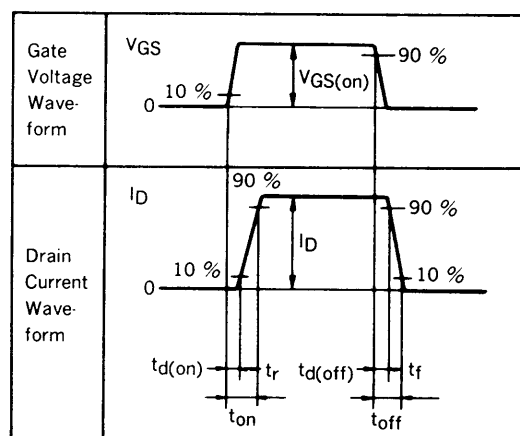
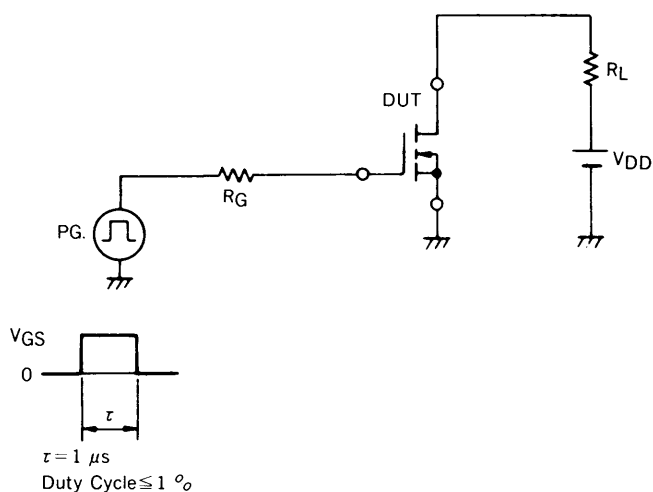
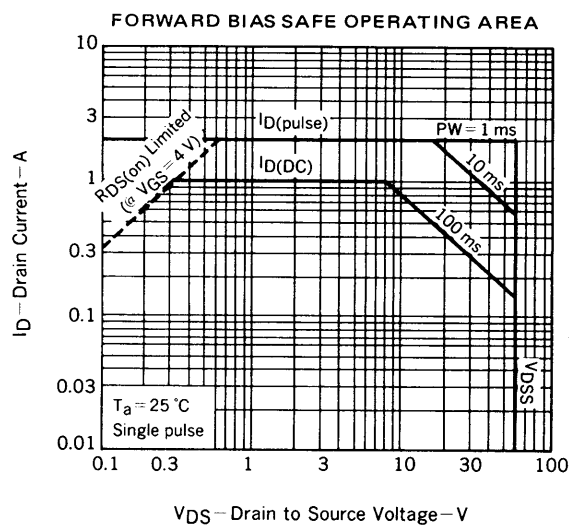
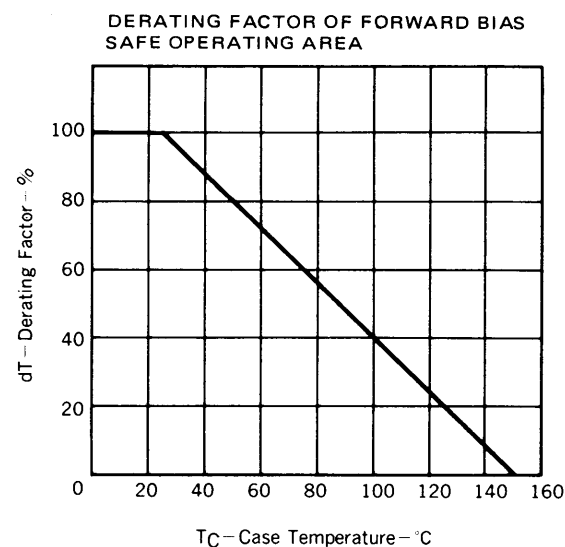
ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

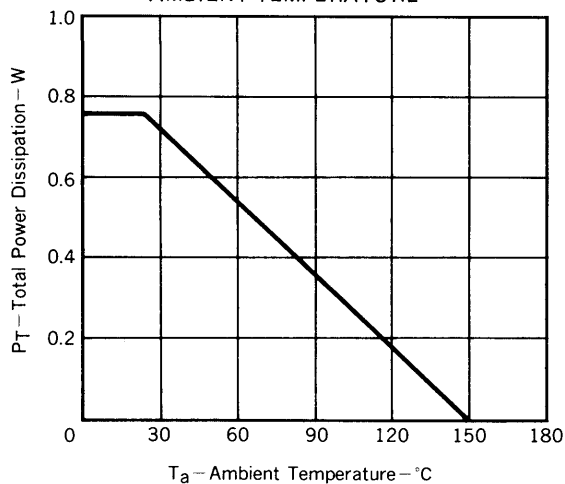
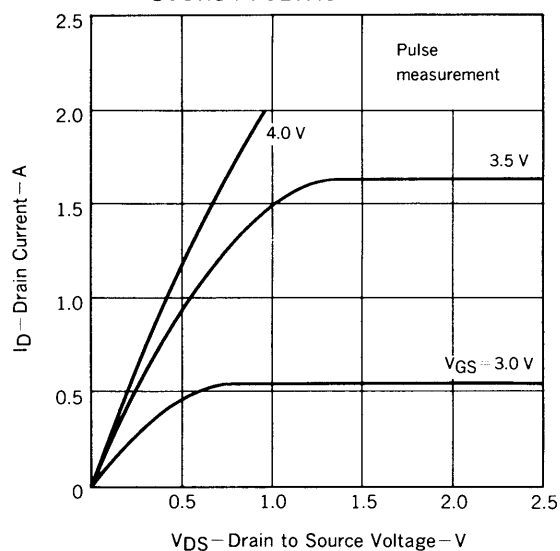
PARAMETER	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	V_{DSS}	60	V	$V_{GS} = 0$
Gate to Source Voltage	V_{GSS}	± 20	V	$V_{DS} = 0$
Drain Current	$I_{D(DC)}$	± 1.0	A	
Drain Current	$I_{D(pulse)}$	± 2.0	A	$PW \leq 10 \text{ ms, Duty Cycle} \leq 50 \%$
Total Power Dissipation	P_T	750	mW	
Channel Temperature	T_{ch}	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$	

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

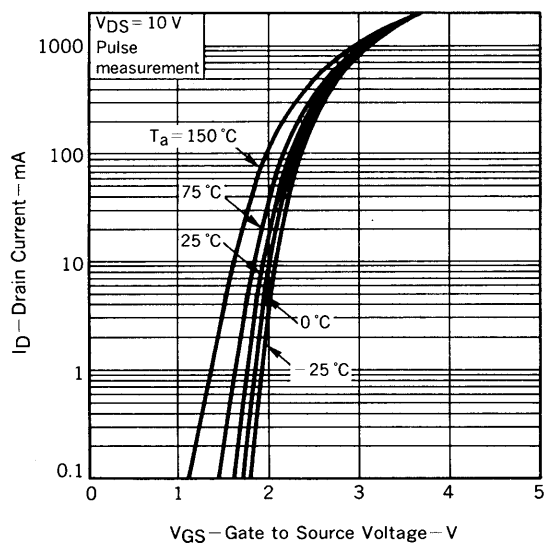
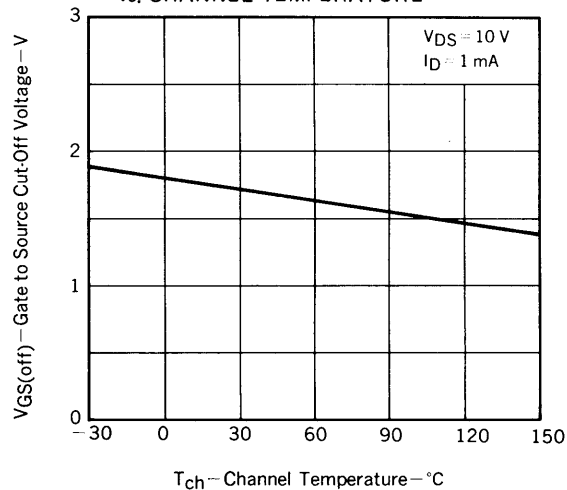
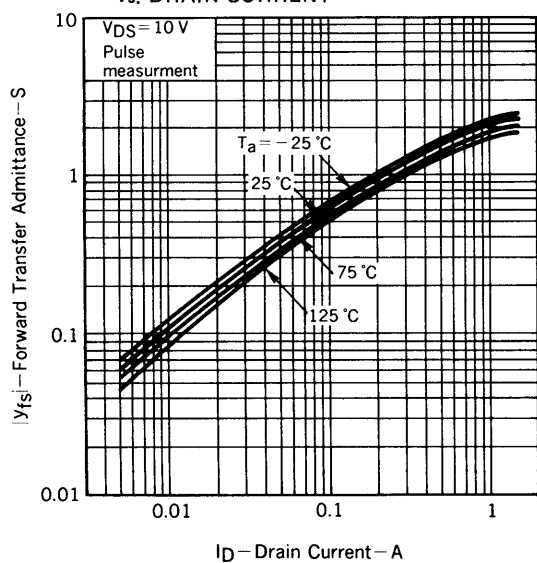
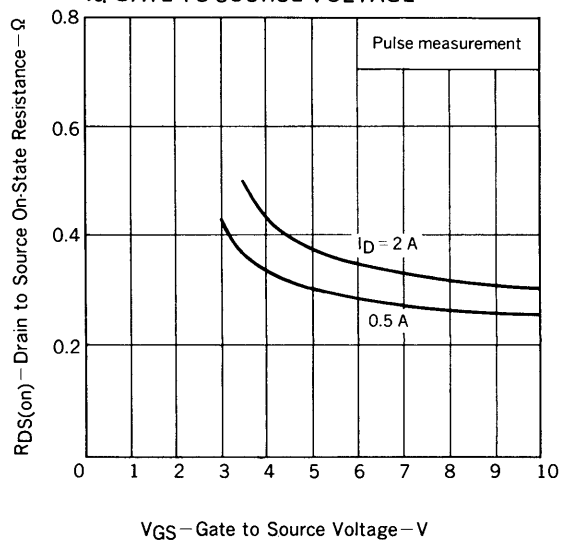
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Cut-off Current	I_{DSS}			10	μA	$V_{DS} = 60\text{ V}, V_{GS} = 0$
Gate Leakage Current	I_{GSS}			± 10	μA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0$
Gate Cut-off Voltage	$V_{GS(off)}$	1.0	1.7	2.5	V	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $	0.4			S	$V_{DS} = 10\text{ V}, I_D = 0.5\text{ A}$
Drain to Source On-State Resistance	$R_{DS(on)1}$		0.31	1.00	Ω	$V_{GS} = 4.0\text{ V}, I_D = 0.5\text{ A}$
Drain to Source On-State Resistance	$R_{DS(on)2}$		0.24	0.65	Ω	$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$
Input Capacitance	C_{iss}		220		pF	$V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$
Output Capacitance	C_{oss}		105		pF	
Feedback Capacitance	C_{rss}		16		pF	
Turn-On Delay Time	$t_{d(on)}$		15		ns	$V_{GS(on)} = 10\text{ V}, R_G = 10\ \Omega$ $V_{DD} = 25\text{ V}, I_D = 0.5\text{ A}$ $R_L = 50\ \Omega$
Rise Time	t_r		35		ns	
Turn-Off Delay Time	$t_{d(off)}$		380		ns	
Fall Time	t_f		120		ns	

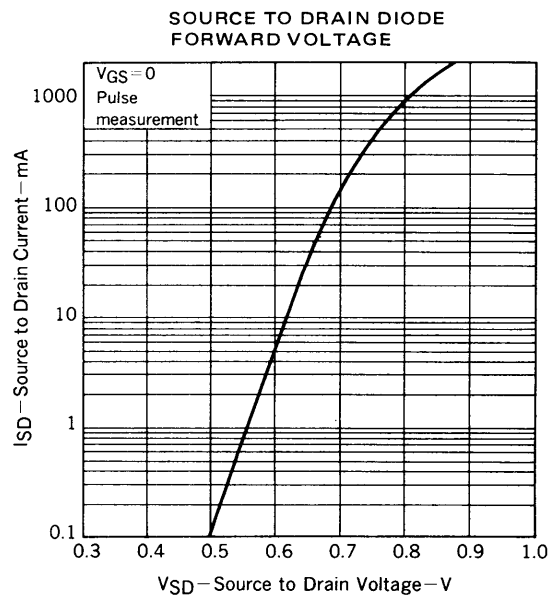
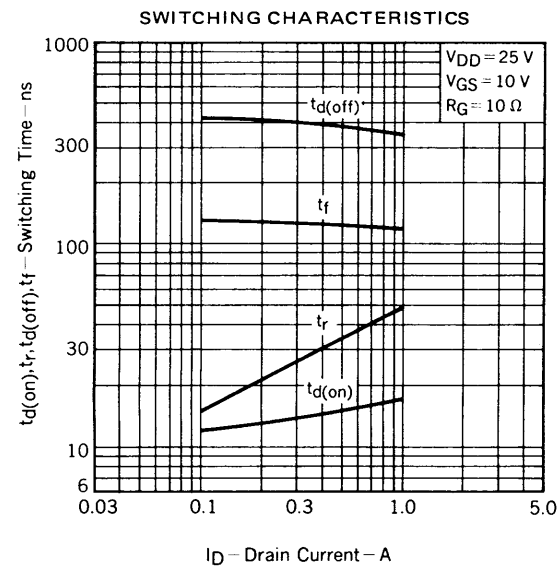
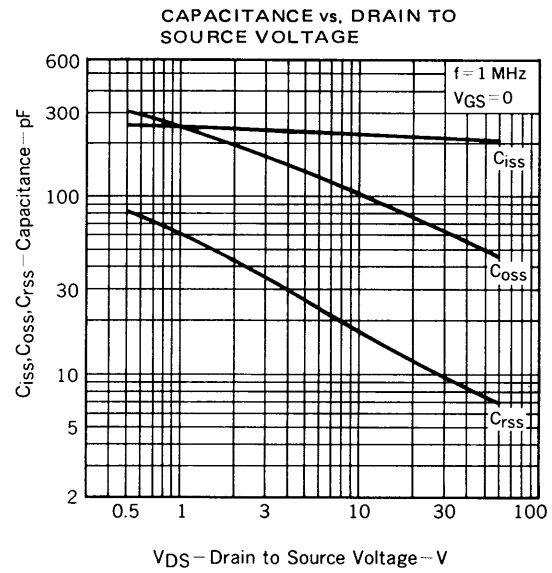
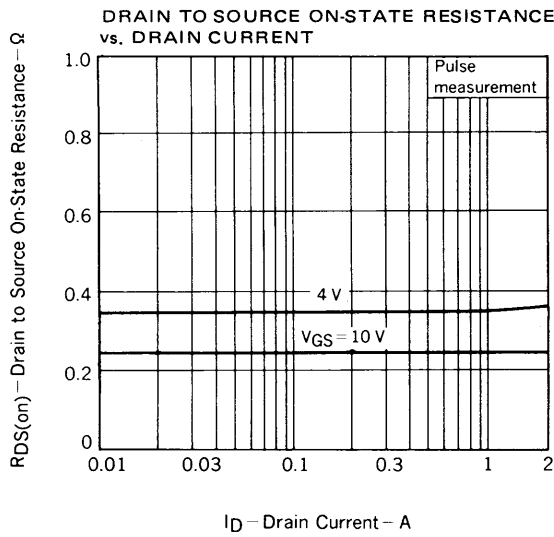
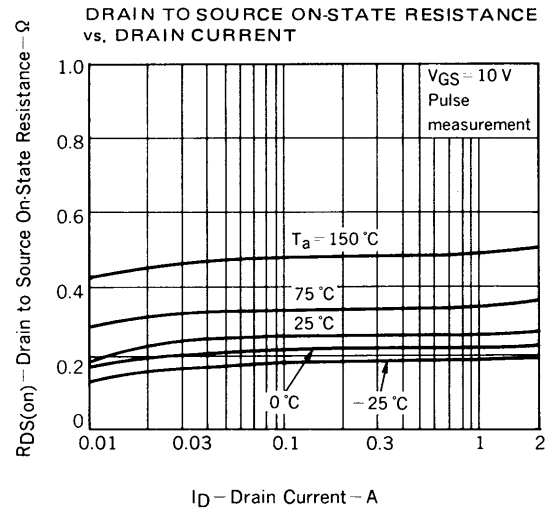
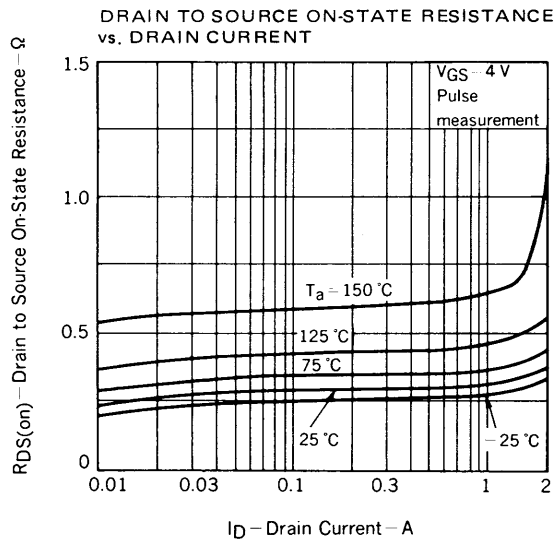
SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

TOTAL POWER DISSIPATION vs.
AMBIENT TEMPERATUREDRAIN CURRENT vs. DRAIN TO
SOURCE VOLTAGE

TRANSFER CHARACTERISTICS

GATE TO SOURCE CUTOFF VOLTAGE
vs. CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE
vs. DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE
vs. GATE TO SOURCE VOLTAGE



RECOMMENDED SOLDERING CONDITIONS

Solder this product under the following recommended conditions.

For soldering methods or soldering conditions other than those recommended in the table, please consult our NEC salespeople.

Insert type

Soldering method	Soldering conditions	Recommended condition code
Wave soldering	Solder bath temperature: 260 °C max. Soldering time: 10 sec max.	

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The devices listed in this document are not suitable for use in the field where very high reliability is required including, but not limited to, aerospace equipment, submarine cables, nuclear reactor control systems and life support systems. If customers intend to use NEC devices for above applications or those intended to use "Standard", or "Special" quality grade NEC devices for the applications not intended by NEC, please contact our sales people in advance.

Application examples recommended by NEC Corporation

Standard: Data processing and office equipment, Communication equipment (terminal, mobile). Test and Measurement equipment, Audio and Video equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Communication equipment (trunk line), Train and Traffic control devices, industrial robots, Burning control systems, antidisaster systems, anticrime systems etc.